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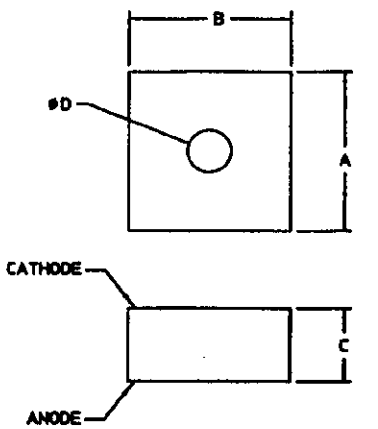
Schottky Zero Bias Detector Diode

MA4E931Z2-1261A

Features

- Can be used without external DC bias
- Exhibits uniform Rv characteristics
- High Voltage Sensititivity
- P Type Schottky Diode
- Available in chip form (ODS-1261)



DIM.	INCHES.		MM	
	MIN.	MAX.	MIN.	MAX.
A	.013	.017	.330	.430
B	.013	.017	.330	.430
C	.006	.008	.152	.203
D	.0035	.0045	.089	.114

Case Style 1261A

Description

This Zero Bias Detector (ZBD) diode is suitable for use in microstrip or stripline detector cuircuits. The 4 mil diameter gold pad and sturdy construction allow you to use these chips in automatic assembly processes.

Applications

Designed for high volume , low cost , detector applications.

Absolute Maximum Ratings

Parameter	Value
Operating Temperature	-65° C to + 150° C
Storage Temperature	-65° C to + 150° C
Reverse Voltage	3 V
Incident RF Power (CW)	75 mW

Exceeding any of these values may result in permanent damage

Electrical Parameters @ 25 Deg. C

DC Parameters

Voltage Breakdown
Vb @ 1 mA = 3.0 volts minimum

Forward Voltage
Vf @ 1 mA = 150 mV typical

RF Parameters

Tangential Signal Sensitivity (TSS)
Test Conditions :
Frequency = 10 GHz , BW=2 MHz
Noise Amplifier = 3.5 Db
Test Specification : - 52 dB min.

Video Impedance (Rv)
Test Conditions :
Frequency = 10 GHz, BW=2 MHz
Test Specification :
2.5 kohms minimum - 4.5 kohms maximum

Voltage Output (Eo)
Test Conditions :
Frequency = 10 GHz, BW=2 MHz
Test Specification : 5.0 mV minimum